

MMBTA55LT1G, MMBTA56LT1G

Driver Transistors

PNP Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage MMBTA55 MMBTA56	V_{CEO}	-60 -80	Vdc
Collector - Base Voltage MMBTA55 MMBTA56	V_{CBO}	-60 -80	Vdc
Emitter - Base Voltage	V_{EBO}	-4.0	Vdc
Collector Current - Continuous	I_C	-500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

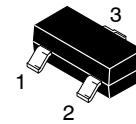
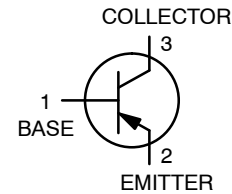
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



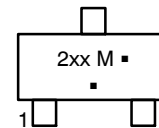
ON Semiconductor®

<http://onsemi.com>



SOT-23
CASE 318
STYLE 6

MARKING DIAGRAM



2xx = Device Code
 x = H for MMBTA55LT1
 xx = GM for MMBTA56LT1
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)
 *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

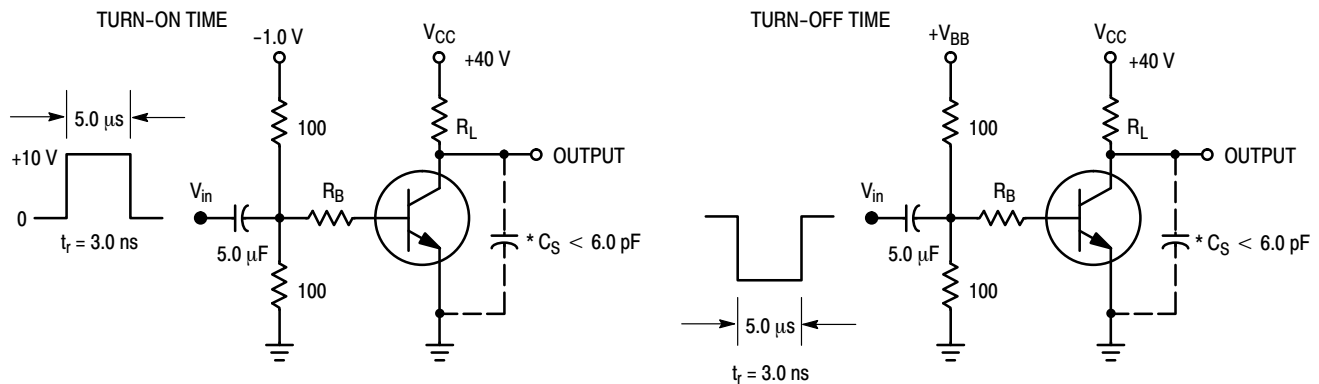
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MMBTA55LT1G, MMBTA56LT1G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector - Emitter Breakdown Voltage (Note 3) ($I_C = -1.0\text{ mA}$, $I_B = 0$)	MMBTA55 MMBTA56 $V_{(BR)CEO}$	-60 -80	-	Vdc
Emitter - Base Breakdown Voltage ($I_E = -100\ \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	-4.0	-	Vdc
Collector Cutoff Current ($V_{CE} = -60\text{ Vdc}$, $I_B = 0$)	I_{CES}	-	-0.1	μA
Collector Cutoff Current ($V_{CB} = -60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = -80\text{ Vdc}$, $I_E = 0$)	MMBTA55 MMBTA56 I_{CBO}	- -	-0.1 -0.1	μA
ON CHARACTERISTICS				
DC Current Gain ($I_C = -10\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$) ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	h_{FE}	100 100	- -	-
Collector - Emitter Saturation Voltage ($I_C = -100\text{ mA}$, $I_B = -10\text{ mA}$)	$V_{CE(sat)}$	-	-0.25	Vdc
Base - Emitter On Voltage ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$)	$V_{BE(on)}$	-	-1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current - Gain - Bandwidth Product (Note 4) ($I_C = -100\text{ mA}$, $V_{CE} = -1.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	50	-	MHz

- Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
- f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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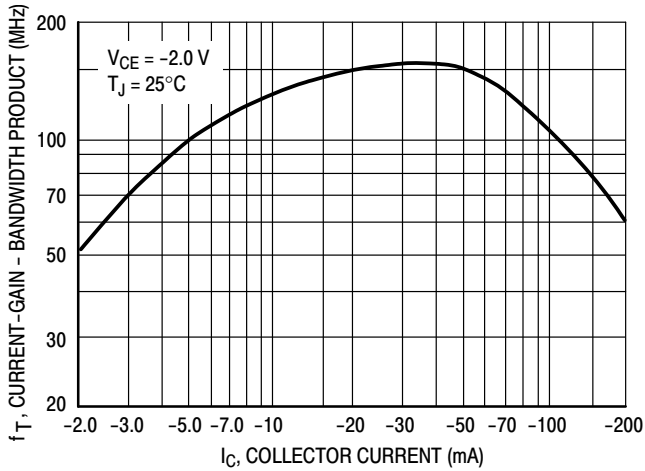


Figure 2. Current-Gain — Bandwidth Product

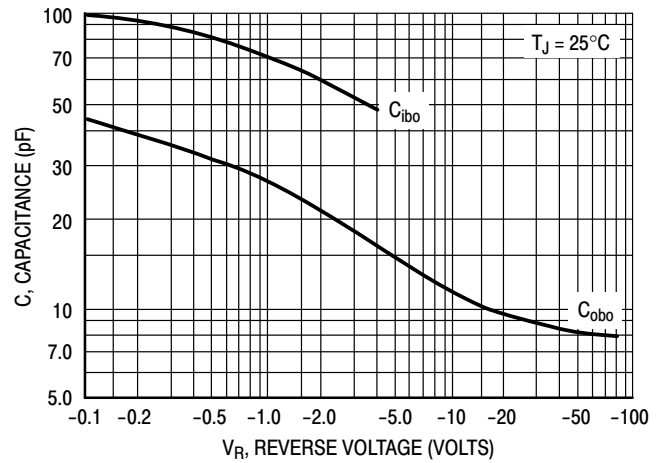


Figure 3. Capacitance

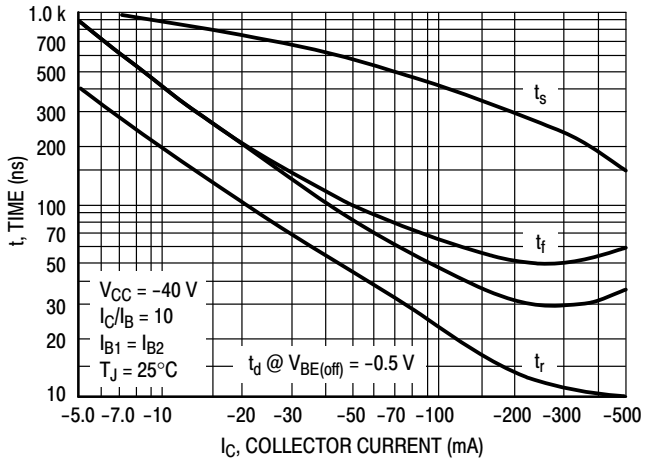


Figure 4. Switching Time

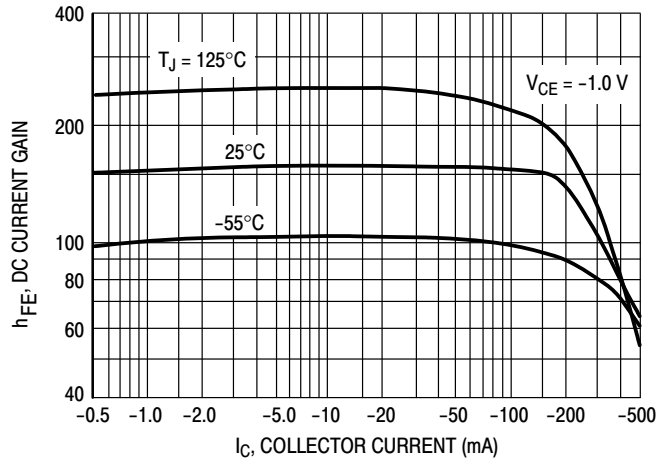


Figure 5. DC Current Gain

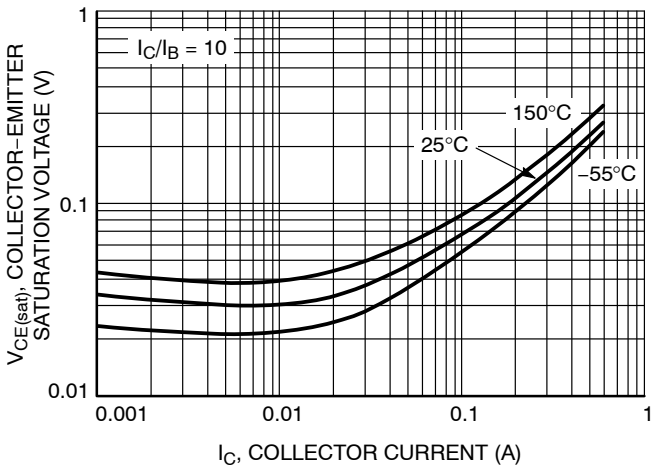


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

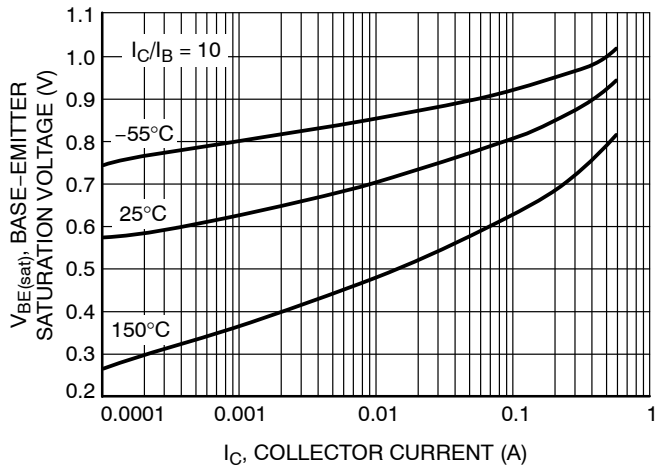


Figure 7. Base Emitter Saturation Voltage vs. Collector Current

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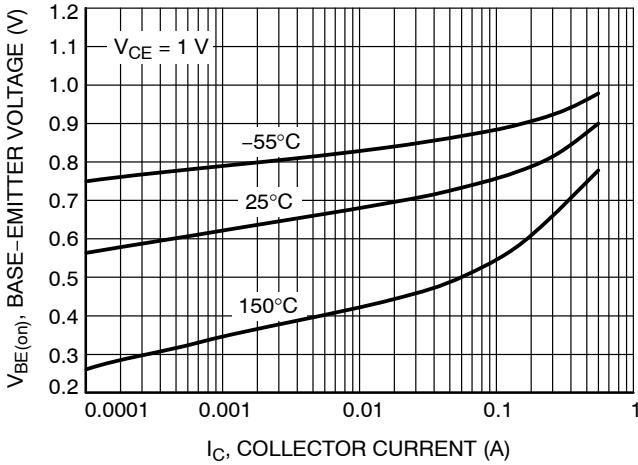


Figure 8. Base Emitter Voltage vs. Collector Current

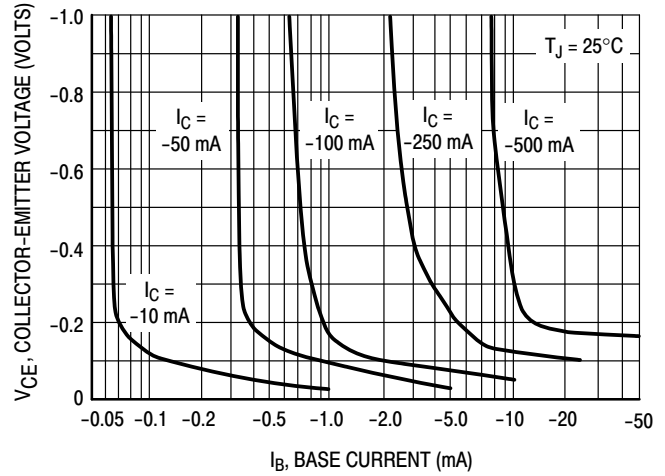


Figure 9. Collector Saturation Region

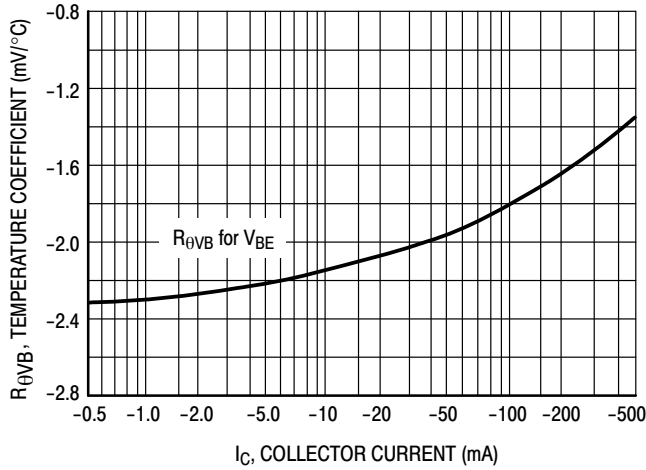


Figure 10. Base-Emitter Temperature Coefficient

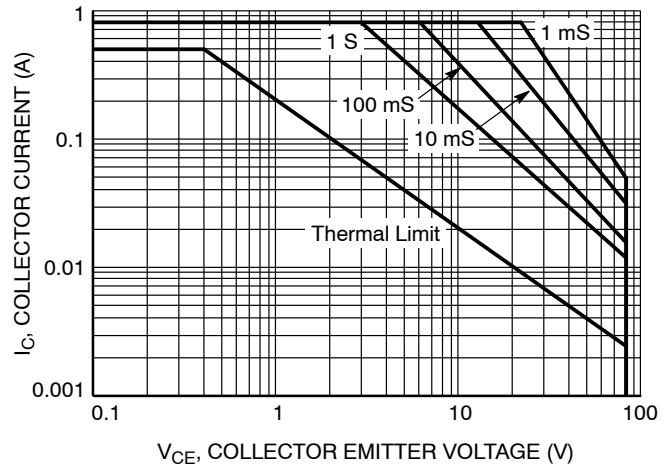


Figure 11. Safe Operating Area

ORDERING INFORMATION

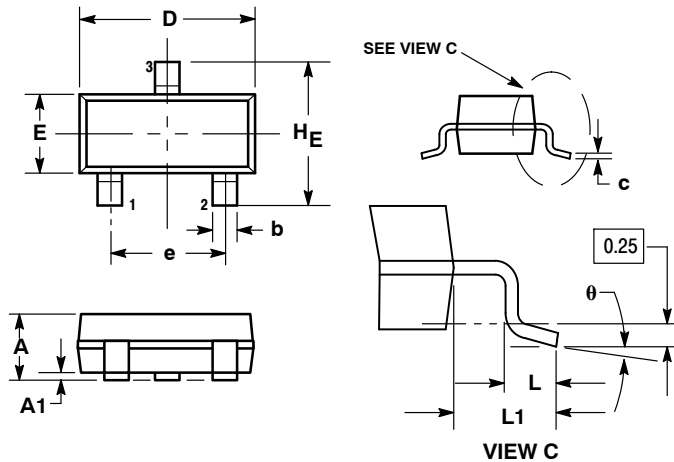
Device Order Number	Package Type	Shipping [†]
MMBTA55LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA55LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA56LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA56LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA55LT1G, MMBTA56LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

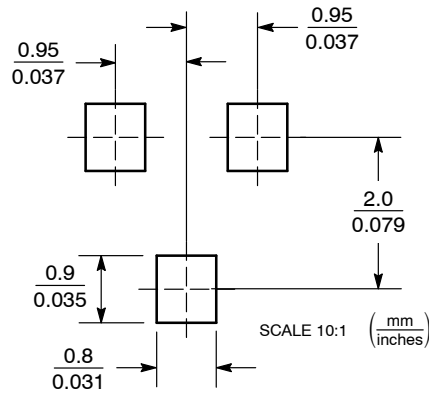
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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